DOCUMENT CHANGE REQUEST

DCR number 430	Changes required for: N/A	Originator: Aissa Nehdi
Date: 2008/09/09	Date sent: 2008/09/09	Organisation: CNES
Status: IMPLEMENTED		

Title:	Transistors High Power PNP, based on type 2N5153		
Number:	5204/002	Issue:	3

Other documents affected:

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Paragraph:

Paragraph 1.4.2 page 5
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Original wording:

Proposed wording:

Variant 07 added (SMD.5) emitter-base inverted versus variant 06

Justification:

In conformity with Mil-PRF-19500/545F

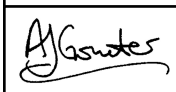
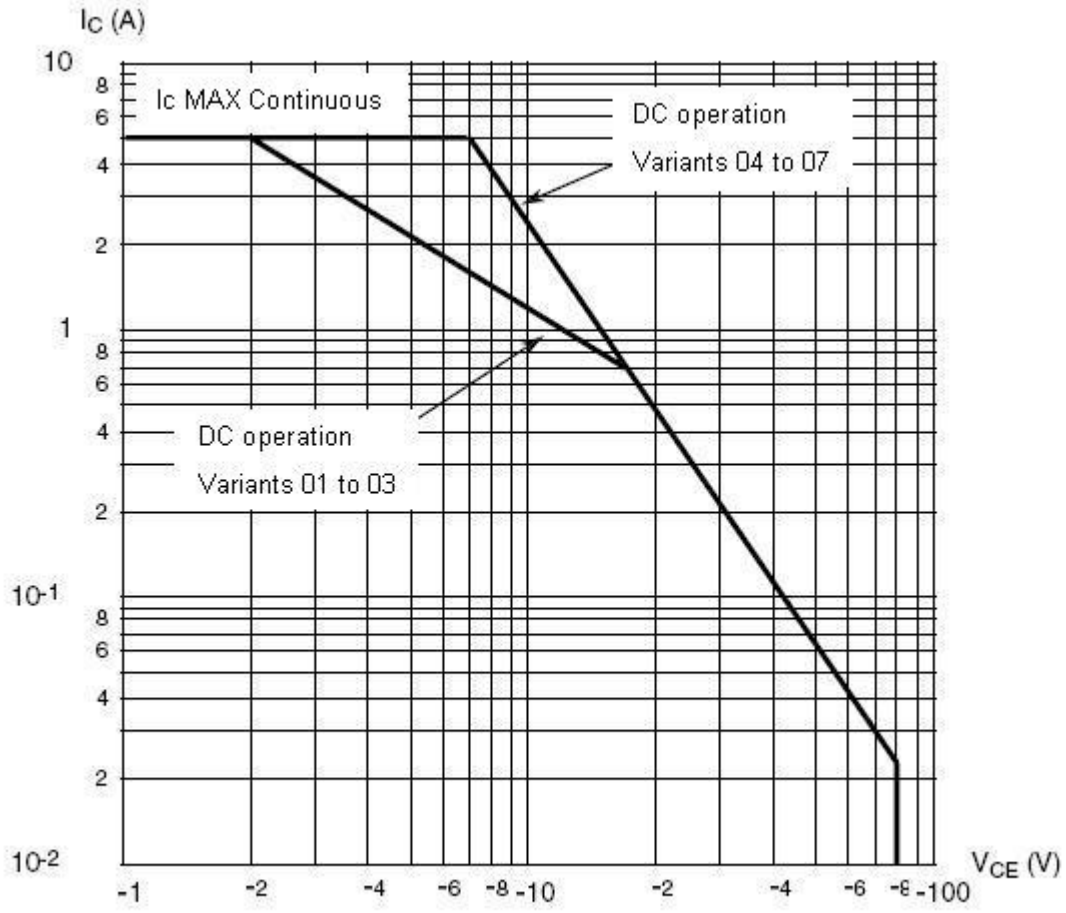
Attachments:
DCR430att.pdf, null
Modifications:
N/A
Approval signature:

Date signed:
2008-09-09

Table 1 (a) Component Type Variants

Variant Number	Based on Type	Case	Lead/Terminal Material and finish	Weight max g
01	2N5153	TO-39	D2	1.5
02	2N5153	TO-39	D3 or D4	1.5
03	2N5153	TO-39	D7	1.5
04	2N5153	TO-257	H2	5
05	2N5153	TO-257	H4	5
06	2N5153	SMD.5	Q14	2
07	2N5153	SMD.5	Q14	2

5. Safe Operating Area applies as follows:

Maximum Safe Operating Area Graph



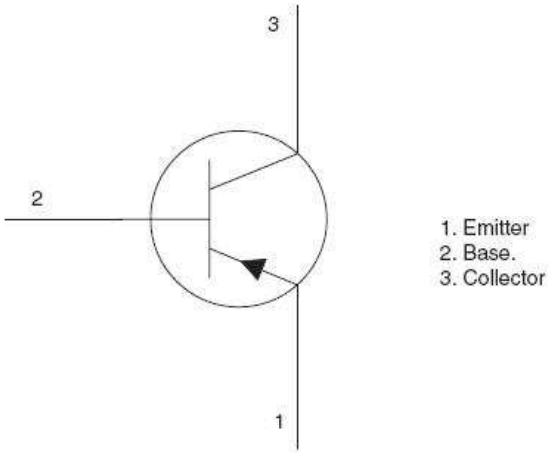
NOTES:

1. Terminal identification is specified by the components geometry where :

Variante 06 Terminal 1 = emitter, Terminal 2 = base and Terminal 3 = collector.
Variante 07 Terminal 1 = base, Terminal 2 = emitter and Terminal 3 = collector.

1.8 FUNCTIONAL DIAGRAM

Variants 01 to 06



Variant 07

